## N-Channel 100-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

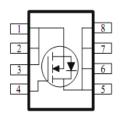
- LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I□ (A)		
100	140 @ V <sub>GS</sub> = 10V	4.9		
	150 @ V <sub>GS</sub> = 4.5V	4.8		









ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter				Limit	Units		
Drain-Source Voltage				100	V		
Gate-Source Voltage				±20	V		
Continuous Drain Course at 8		T <sub>A</sub> =25°C	_	4.9	А		
Continuous Drain Current a		T <sub>A</sub> =70°C	I <sub>D</sub>	4			
Pulsed Drain Current <sup>b</sup>				20	'		
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	6.1	Α				
Down Dissipation 8		$T_A=25$ °C $T_A=70$ °C	$P_{D}$	5	W		
Power Dissipation <sup>a</sup>			' D	3.2	V V		
Operating Junction and Storage Temperature Range				-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

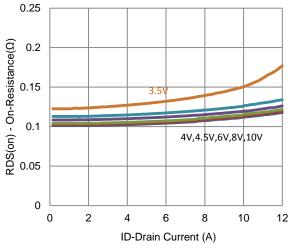
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zoro Coto Voltago Drain Current		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	10		uA		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	7.5			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_D = 3.9 \text{ A}$			140	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 3.2 \text{ A}$			150	11177	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 3.9 \text{ A}$		9		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 3.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.81		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V},$		10		nC	
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 30 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 3.9 \text{ A}$		3.7			
Gate-Drain Charge	$Q_gd$	1B = 3.3 A		3.5			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 50 \text{ V}, R_1 = 12.9 \Omega,$		6			
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, R_L - 12.9 \Omega,$ $I_D = 3.9 \text{ A},$		5		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		32			
Fall Time	t <sub>f</sub>	V GEN = 10 V, 1 (GEN = 0.22		8			
Input Capacitance	C <sub>iss</sub>	_		1621			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		66		pF	
Reverse Transfer Capacitance	$C_{rss}$			47			

#### Notes

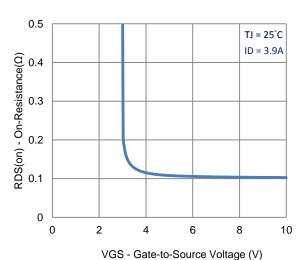
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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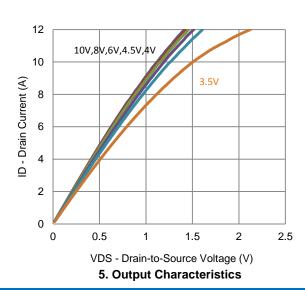
### **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



10

TJ = 25°C

8

(Y)

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4

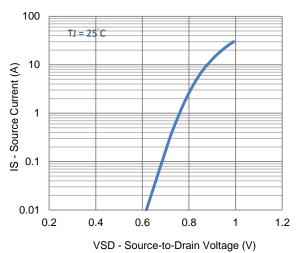
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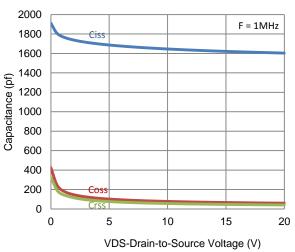
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VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

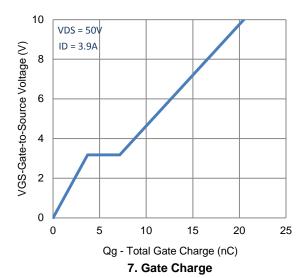


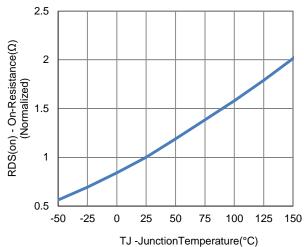
4. Drain-to-Source Forward Voltage

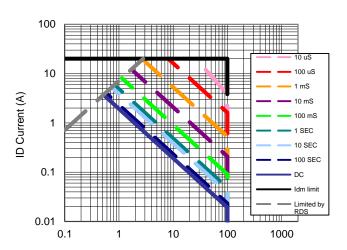


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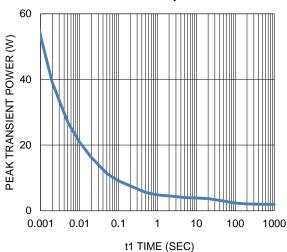
### **Typical Electrical Characteristics**







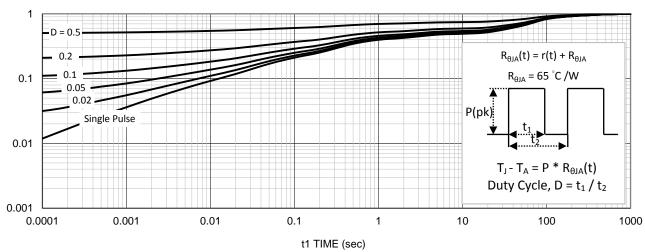
8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

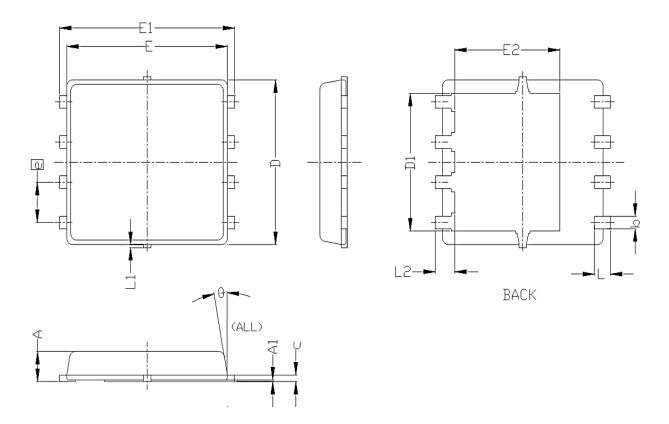
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# Package Information



SYMBOLS DIMENSION		ONS IN MILLIMETERS		DIMENSIONS IN INCHES			
STMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0. 039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е		5.55 BSC			0.219 BSC		
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	